

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Claims.

X1
11. (Amended) The method of claim 10, further including:

the feature can vary according to a different trench depth; and

5 depositing the first layer to a predetermined thickness equivalent to a desired trench depth.

12. The method of claim 11, further including:

10 forming the etch stop layer comprising silicon dioxide on a semiconductor substrate; and

depositing the first layer includes depositing a layer comprising polysilicon having a thickness less than 5000 angstroms.

X2
13. (Amended) The method of claim 10, further including:

15 the process to be monitored forms the non-monitor trench in a normal wafer; and

the monitor wafer is a non semiconductor-on-insulator (SOI) wafer and the normal wafer is a SOI wafer having semiconductor islands of a predetermined thickness; and

20 depositing the first layer of the predetermined thickness.

X3
16. (Amended) The method of claim 10, wherein:

etching the first layer includes substantially anisotropically etching with a selectivity between the first layer and the etch stop layer of greater than 30:1.